





P-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance:
 - $R_{DS(ON)} < 77m\Omega @ V_{GS} = -10V$
 - $R_{DS(ON)} < 95m\Omega @ V_{GS} = -4.5V$
 - $R_{DS(ON)} < 150 \text{m}\Omega$ @ $V_{GS} = -2.5V$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

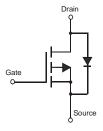
Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)

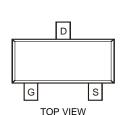
SOT-23







Equivalent Circuit



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Drain Source Voltage		V_{DSS}	-30	V
Gate-Source Voltage		V_{GSS}	±12	V
Drain Current (Note 1)	$T_A = 25$ °C $T_A = 70$ °C	I _D	-3.5 -2.8	А
Drain Current (Note 1)	Pulsed	I _{DM}	-12	А
Body-Diode Continuous Current (Note 1)		Is	-2.0	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	P_{D}	1.4	W
Thermal Resistance, Junction to Ambient @T _A = 25°C (Note 1)	$R_{ hetaJA}$	90	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

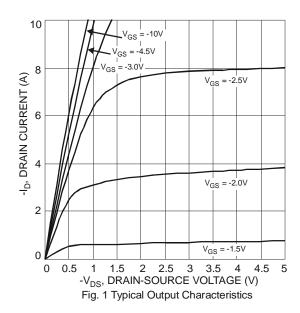
- 1. Device mounted on FR-4 PCB. $t \le 5$ sec.
- 2. No purposefully added lead.
- 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

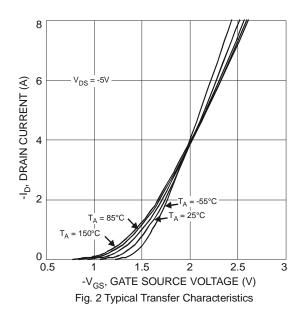


Electrical Characteristics @T_A = 25°C unless otherwise specified

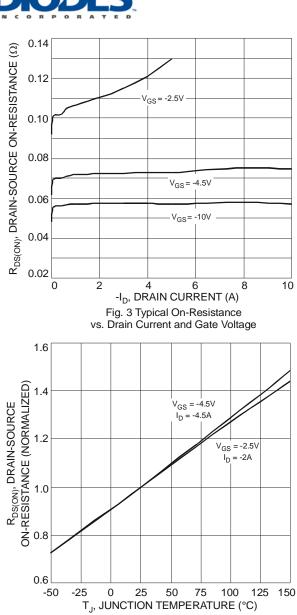
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 4)							
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Body Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 4)					_		
Gate Threshold Voltage	V _{GS(th)}	-0.6	_	-1.3	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
Static Drain-Source On-Resistance	R _{DS} (ON)		59 73 115	77 95 150	mΩ	$V_{GS} = -10V$, $I_D = -4.2A$ $V_{GS} = -4.5V$, $I_D = -4A$ $V_{GS} = -2.5V$, $I_D = -3A$	
Forward Transconductance	9fs		8		S	$V_{DS} = -5V, I_{D} = -4A$	
Source-Drain Diode Forward Voltage	V_{SD}		0.8	-1.25	V	$V_{GS} = 0V, I_{S} = -3.0A$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	Ciss	_	432	_	pF	45)/)/ 2)/	
Output Capacitance	Coss		87		pF	$V_{DS} = -15V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}		62		pF	1 – 1.0ivii iz	
Gate Resistance	R_{G}		4.04	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$ f = 1.0MHz	
SWITCHING CHARACTERISTICS	,						
Total Gate Charge	Q_G		5.9 12	_	nC	$V_{DS} = -15V$, $V_{GS} = -4.5V$, $I_{D} = -4.0A$ $V_{DS} = -15V$, $V_{GS} = -10V$, $I_{D} = -4.0A$	
Gate-Source Charge	Q_{GS}		1.0		nc nc	V _{DS} = -15V, V _{GS} = -4.5V, I _D = -4.0A	
Gate-Drain Charge	Q_{GD}		3.1	_		$V_{DS} = -15V$, $V_{GS} = -4.5V$, $I_{D} = -4.0A$	
Turn-On Delay Time	t _{d(on)}		4.6				
Rise Time	t _r		6.5		ns	$V_{DS} = -15V$, $V_{GS} = -10V$,	
Turn-Off Delay Time	t _{d(off)}	_	27.8	_	115	$I_D = -1A, R_G = 6.0\Omega$	
Fall Time	t _f	_	15.0	_			

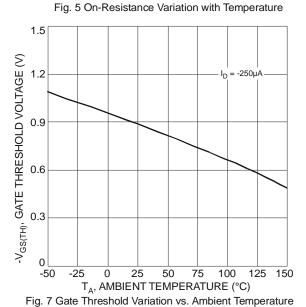
Notes: 4. Short duration pulse test used to minimize self-heating effect.











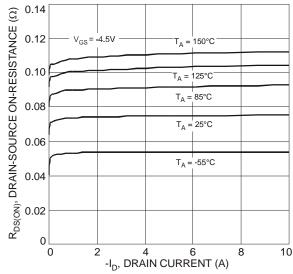
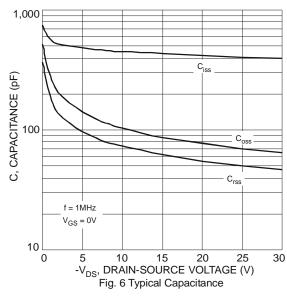


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature



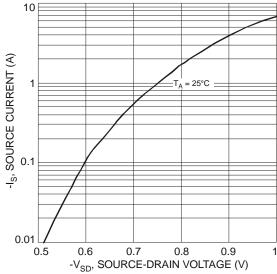


Fig. 8 Diode Forward Voltage vs. Current



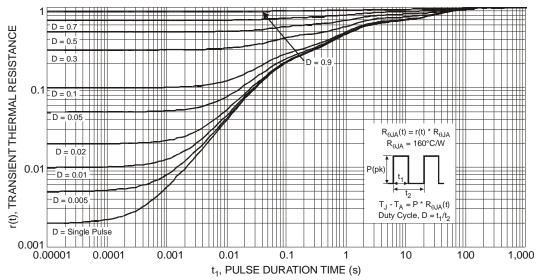


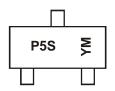
Fig. 9 Transient Thermal Response

Ordering Information (Note 5)

Part Number	Case	Packaging
DMP3130L-7	SOT-23	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

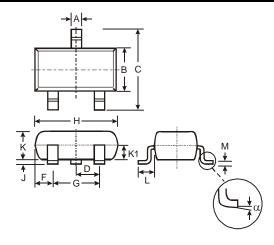


P5S = Product Type Marking Code YM = Date Code Marking Y = Year (ex: V = 2008) M = Month (ex: 9 = September)

Date Code Key

Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	Х		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

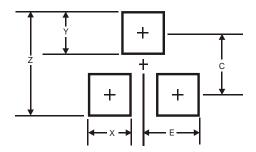
Package Outline Dimensions



SO1-23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.903	1.10	1.00			
K1	-	-	0.400			
L	0.45	0.61	0.55			
M	0.085	0.18	0.11			
α	0°	8°	-			
All	All Dimensions in mm					



Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35

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